High Voltage Diode Module (TRACTION - PAC ${ }^{\text {TM }}$ )

Preliminary Data Sheet

| $\mathrm{V}_{\text {RSM }}$ | $\mathbf{V}_{\text {RRM }}$ | Type |
| :---: | :---: | :--- |
| $\mathrm{V}^{2}$ | $\mathrm{~V}^{2}$ |  |
| 700 | 600 | PSTKD 82/06 |
| 900 | 800 | PSTKD 82/08 |
| 1100 | 1000 | PSTKD 82/10 |
| 1300 | 1200 | PSTKD 82/12 |
| 1500 | 1400 | PSTKD 82/14 |
| 1700 | 1600 | PSTKD 82/16 |
| 1900 | 1800 | PSTKD 82/18 |


| Symbol | Test Conditions |  | Maximum Ratings |  |
| :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\text {FRMS }}$ | $\begin{aligned} & \mathrm{T}_{\mathrm{vJ}}=\mathrm{T}_{\text {vjM }} \\ & \mathrm{T}_{\mathrm{C}}=110^{\circ} \mathrm{C} ; 180^{\circ} \text { sine } \end{aligned}$ |  | 180 | A |
| $\mathrm{I}_{\text {favm }}$ |  |  | 82 | A |
| $\mathrm{I}_{\text {TSM }}$ | $\mathrm{T}_{\mathrm{VJ}}=45^{\circ} \mathrm{C}$; | $\mathrm{t}=10 \mathrm{~ms}(50 \mathrm{~Hz})$ | 1700 | A |
|  | $V_{R}=0$ | $\mathrm{t}=8.3 \mathrm{~ms}(60 \mathrm{~Hz})$ | 1950 | A |
|  | $\mathrm{T}_{\mathrm{V},}=\mathrm{T}_{\mathrm{VJM}}$ | $\mathrm{t}=10 \mathrm{~ms}(50 \mathrm{~Hz})$ | 1530 | A |
|  | $V_{R}=0$ | $\mathrm{t}=8.3 \mathrm{~ms}(60 \mathrm{~Hz})$ | 1740 | A |
| òi $^{2} \mathrm{dt}$ | $\mathrm{T}_{\mathrm{V},}=45^{\circ} \mathrm{C}$ | $\mathrm{t}=10 \mathrm{~ms}(50 \mathrm{~Hz})$ | 14450 | $A^{2} \mathrm{~s}$ |
|  | $V_{R}=0$ | $\mathrm{t}=8.3 \mathrm{~ms}(60 \mathrm{~Hz})$ | 15700 | $A^{2} \mathrm{~S}$ |
|  | $\mathrm{T}_{\mathrm{VJ}}=\mathrm{T}_{\mathrm{VJM}}$ | $\mathrm{t}=10 \mathrm{~ms}(50 \mathrm{~Hz})$ | 11700 | $A^{2} \mathrm{~s}$ |
|  | $V_{R}=0$ | $\mathrm{t}=8.3 \mathrm{~ms}(60 \mathrm{~Hz})$ | 12500 | $A^{2} \mathrm{~s}$ |
| $\mathrm{T}_{\text {vv }}$ |  |  | -40 ... 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{vJM}}$ |  |  | 125 | ${ }^{\circ} \mathrm{C}$ |
|  |  |  | -40 ... 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{V}_{\text {ISOL }}$ | $50 / 60 \mathrm{~Hz}$, RMS $\mathrm{t}=1 \mathrm{~min}$ |  | 3000 | V |
|  | $\mathrm{l}_{\text {ISOL }} \leq 1 \mathrm{~mA}$ | $\mathrm{t}=1 \mathrm{~s}$ | 3600 | V~ |
| $\overline{M_{d}}$ | Mounting torque (M5) |  | 5.0/44 | Nm/lb.in. |
|  | Terminal connection torque (ISK M5)Typical including screws |  | 3.0/26 | Nm/lb.in. |
| Weight |  |  | 56 | g |


| Symbol | Test Conditions | Characteristic | alues |
| :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\text {RRM }}, \mathrm{I}_{\text {DRM }}$ | $\mathrm{T}_{\mathrm{VJ}}=\mathrm{T}_{\mathrm{VJM}} ; \mathrm{V}_{\mathrm{R}}=\mathrm{V}_{\text {RRM }}$ | 15 | mA |
| $\mathrm{V}_{\text {T }}$ | $\mathrm{I}_{\mathrm{T}}=200 \mathrm{~A} ; \mathrm{T}_{\mathrm{VJ}}=25^{\circ} \mathrm{C}$ | 1.74 | V |
| $\overline{V_{\text {т }}}$ | For power-loss calculations only ( $\mathrm{T}_{\mathrm{VJ}}=\mathrm{T}_{\mathrm{VJM}}$ ) $\mathrm{T}_{\mathrm{V} J}=\mathrm{T}_{\mathrm{V} \mathrm{JM}}$ | 0.8 2.7 | $\begin{gathered} \mathrm{V} \\ \mathrm{~m} \Omega \end{gathered}$ |
| $\begin{aligned} & \begin{array}{l} \mathbf{Q}_{\mathrm{s}} \\ \mathrm{I}_{\mathrm{RM}} \end{array} \end{aligned}$ | $\mathrm{T}_{\mathrm{VJ}}=125^{\circ} \mathrm{C} ; \mathrm{I}_{\mathrm{F}}=50 \mathrm{~A},-\mathrm{di} / \mathrm{dt}=3 \mathrm{~A} / \mu \mathrm{s}$ | $\begin{array}{r} 170 \\ 45 \end{array}$ | $\begin{gathered} \mu \mathrm{C} \\ \mathrm{~A} \end{gathered}$ |
| $\mathrm{R}_{\text {thJc }}$ | per diode; DC current per module | 0.35 0.18 | K/W K/W |
| $\mathbf{R}_{\text {thJk }}$ | per module <br> per diode; DC current per module | $\begin{array}{r} 0.18 \\ 0.55 \\ 0.275 \end{array}$ | $\begin{aligned} & \text { K/W } \\ & \text { K/W } \end{aligned}$ K/W |
| $\mathrm{d}_{\text {s }}$ | Creeping distance on surface | 12.7 | mm |
| $\mathrm{d}_{\mathrm{A}}$ | Creepage distance in air | 9.6 | mm |
| a | Maximum allowable acceleration | 50 | $\mathrm{m} / \mathrm{s}^{2}$ |

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.
$\mathrm{I}_{\text {frus }}=8180 \mathrm{~A}$
$\mathrm{I}_{\text {FAVM }}=82 \mathrm{~A}$
$\mathrm{~V}_{\text {RRM }}=600-1800 \mathrm{~V}$


## Features

- International standard package, JEDEC TO-240 AA
- Direct Copper Bonded $\mathrm{Al}_{2} \mathrm{O}_{3}$-ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V ~


## Applications

- Supplies for DC power equipment
- DC supply for PWM inverter
- Field supply for DC motors
- Battery DC power supplies


## Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling
- Reduced protection circuits

Dimensions in mm ( $1 \mathrm{~mm}=0.0394$ ")





Fig. 1 Surge overload current $I_{\text {FSM }}$ : Crest value, t: duration


Fig. 2 $\mathrm{ji}^{2} \mathrm{dt}$ versus time ( $1-10 \mathrm{~ms}$ )




Fig. 2a Maximum forward current at case temperature

Fig. 3 Power dissipation versus forward current and ambient temperature (per diode)

Fig. 4 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature
R = resistive load
$L=$ inductive load

$4 z_{\text {two }}$


Fig. 5 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

Fig. 6 Transient thermal impedance junction to case (per diode)
$R_{\text {thuc }}$ for various conduction angles d :

| d | $\mathrm{R}_{\text {thJc }}(\mathrm{K} / \mathrm{W})$ |
| :---: | :--- |
| DC | 0.35 |
| $180^{\circ}$ | 0.37 |
| $120^{\circ}$ | 0.39 |
| $60^{\circ}$ | 0.43 |
| $30^{\circ}$ | 0.47 |

Constants for $\mathrm{Z}_{\mathrm{thJC}}$ calculation:

| i | $\mathrm{R}_{\text {thi }}(\mathrm{K} / \mathrm{W})$ | $\mathrm{t}_{\mathrm{i}}(\mathrm{s})$ |
| :--- | :--- | :--- |
| 1 | 0.013 | 0.0014 |
| 2 | 0.072 | 0.062 |
| 3 | 0.265 | 0.375 |

Fig. 7 Transient thermal impedance junction to heatsink (per diode)
$\mathrm{R}_{\mathrm{thJk}}$ for various conduction angles d :

| d | $\mathrm{R}_{\mathrm{thJK}}(\mathrm{K} / \mathrm{W})$ |
| :---: | :--- |
| DC | 0.55 |
| $180^{\circ}$ | 0.57 |
| $120^{\circ}$ | 0.59 |
| $60^{\circ}$ | 0.63 |
| $30^{\circ}$ | 0.67 |

Constants for $Z_{\text {thJk }}$ calculation:

| i | $\mathrm{R}_{\text {thi }}(\mathrm{K} / \mathrm{W})$ | $\mathrm{t}_{\mathrm{i}}(\mathrm{s})$ |
| :--- | :--- | :--- |
| 1 | 0.013 | 0.0014 |
| 2 | 0.072 | 0.062 |
| 3 | 0.265 | 0.375 |
| 4 | 0.2 | 1.32 |

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